Products

WANGLING

Teflon ceramic dielectric substrate TF-1/2

TF-1/2 is a kind of circuit laminate based on the Teflon (which have excellent microwave and temperature resistance performance) compound with ceramic. This kind of laminate can be comparable with the products (such as RT/duroid 6006/6010/TMM10) from Rogers Corporation in United State of America.

The advantage of design for microwave circuit using TF-1/2 here:

- The operating temperature is much higher than TP-series. It is applicable to long-term operation within temperature ranger of $-80\,^{\circ}\text{C} \sim +200\,^{\circ}\text{C}$, and can be used for wave-welding and melt-back welding.
- Used for the manufacturing of the microwave and millimeter wave printed circuit board.
- Better radiation performance, 30min20rad/cm².
- Dielectric property is stable and has a slight variation with the rise of temperature and frequency. (ϵ r=3.0, 6.0, 9.2, 9.6, 10.2, 16, 20, 22)

Appearance	Meet the general requirement for laminate of microwave PCB.								
Dimension (mm)	150×150 250×250								
Mechanical Strength	Thickness and tolerance are same as TP-series. For special dimension, customized laminates is available.								
Chemical	Peel strength		≥ 8N/cm						
Property	Warp		Same as TP-series.						
	Cutting/punching		No burrs after cutting, minimum space between two punching holes is 0.55mm.						
Electrical Property	Strength		punching notes is 0.55mm.						
	According to the properties of laminate, the chemical etching method for PCB can be used. The dielectric properties of laminate are not changed. The plating through hole can be done.								
	Name	Test condition		Unit	Value				
	Density	Normal state		g/ cm3	2.0~3.5				
	Moisture Absorption	Dip in the distilled water of $20\pm2^{\circ}$ C for 24 hours		%	≤0.02				
	Operating Temperature	High-low temperature chamber		°C	-80°C ~+260°C				
	Thermal Conductivity			W/m/k	0.5				
	СТЕ	-55~28	8℃	ppm/°C	50 (x)				
					50 (y)				

					60 (z)
	Shrinkage Factor	2 hours in boiling water		%	0.0001
	Surface Resistivity	500V	Normal state	Μ • Ω	≥1×105
		DC	Constant humidity and temperature		≥1×103
	Volume Resistivity	Normal stat	te	MΩ.cm	≥1×105
		Constant hutemperature	nmidity and		≥1×104
	Pin Resistance	500VDC	Normal state	ΜΩ	≥1×106
			Constant humidity and temperature	-	≥1×104
	Surface dielectric	Normal stat	te	d=1mm (Kv/mm)	≥1.6
	strength	Constant hutemperature	nmidity and		≥1.4
	Dielectric Constant	10GHZ		ε τ	3.0; 6.0; 9.2; 9.6; 10.2; 16; 20; 22 (±2%)(can be customized)
	Dissipation	10GHZ		tg δ (3~11)	